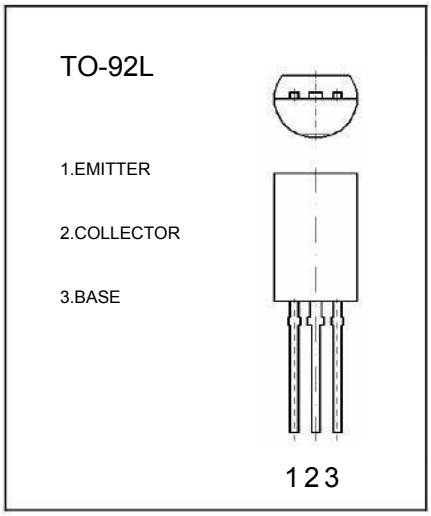
TO-92L Plastic-Encapsulate Transistors

A916 TRANSISTOR (PNP)



FEATURES

Low collector to emitter saturation voltage $V_{CE(sat)}$.
Complementary pair with C1941

MAXIMUM RATINGS (T_A=25℃ unless otherwise noted)

Symbol	Parameter			Units
V_{CBO}	Collector-Base Voltage		-160	V
V_{CEO}	Collector-Emitter Voltage		-160	V
V_{EBO}	Emitter-Base Voltage	-5		V
I_C	Collector Current –Continuous	-0.05		A
P_C	Collector Power Dissipation	1		W
T_J	Junction Temperature	150		℃
T_{stg}	Storage Temperature	-55-150		℃

ELECTRICAL CHARACTERISTICS (Tamb=25℃ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Emitter cut-off current	I_{EBO}	V_{EB}= -5V，I_C=0			-100	μA
Collector cut-off current	I_{CBO}	V_{CB}=-160V, I_E=0			-100	μA
DC current gain	$h_{FE(1)}$	V_{CE}=-10V, I_C=-10mA	90	200	400	
DC current gain	$h_{FE(2)}$	V_{CE}=-10V, I_C=-1mA	50	200		
Collector-emitter saturation voltage	$V_{CE(sat)}$	I_C=-20mA, I_B=-2mA		-0.18	-0.6	V
Base-emitter saturation voltage	$V_{BE(sat)}$	I_C=-20mA, I_B=-2mA		-0.79	-1.0	V

CLASSIFICATION OF $h_{FE(1)}$

Rank	M	L	K
Range	90-180	135-270	200-400